Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

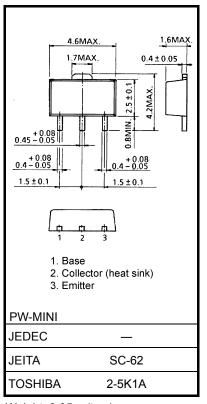
2SA1213

Power Amplifier Applications Power Switching Applications

- Low saturation voltage: $V_{CE (sat)} = -0.5 \text{ V (max) (IC} = -1 \text{ A)}$
- High speed switching time: $t_{stg} = 1.0 \mu s$ (typ.)
- Small flat package
- PC = 1.0 to 2.0 W (mounted on a ceramic substrate)
- Complementary to 2SC2873

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	-50	V	
Collector-emitter voltage	V _{CEO}	-50	V	
Emitter-base voltage	V _{EBO}	-5	V	
Collector current	IC	-2	Α	
Base current	ΙΒ	-0.4	Α	
Collector power dissipation	PC	500	mW	
	PC	1000		
	(Note 1)	1000		
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	−55 to 150	°C	



Weight: 0.05 g (typ.)

Note 1: Mounted on a ceramic substrate (250 mm² × 0.8 t)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

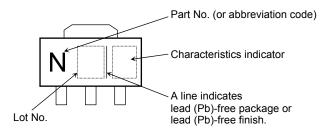


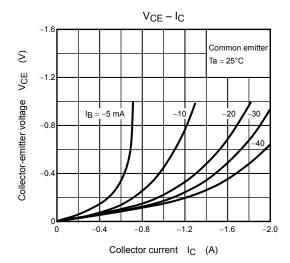
Electrical Characteristics (Ta = 25°C)

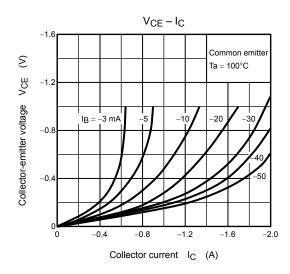
Charact	teristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off cur	rent	I _{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-0.1	μΑ
Emitter cut-off current		I _{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$	_	_	-0.1	μA
Collector-emitter breakdown voltage		V (BR) CEO	I _C = -10 mA, I _B = 0	-50	_	_	V
DC current gain		h _{FE (1)} (Note 3)	V _{CE} = -2 V, I _C = -0.5 A	70	_	240	
		h _{FE (2)}	V _{CE} = -2 V, I _C = -2.0 A	20	_	_	
Collector-emitter sa	turation voltage	V _{CE} (sat)	I _C = -1 A, I _B = -0.05 A	_	_	-0.5	V
Base-emitter satura	ition voltage	V _{BE} (sat)	I _C = -1 A, I _B = -0.05 A	_	_	-1.2	V
Transition frequency		f _T	V _{CE} = -2 V, I _C = -0.5 A	_	120	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	_	40	_	pF
Switching time	Turn-on time	t _{on}	$\begin{array}{c c} I_{B2} & \text{OUTPUT} \\ \hline I_{B1} & \text{INPUT} & \\ \hline I_{B1} & \text{INPUT} \\ \hline 20 \ \mu s & \\ \hline -30 \ V \\ \hline -I_{B1} = I_{B2} = 0.05 \ A, \\ \hline DUTY CYCLE \leq 1\% \\ \end{array}$	ı	0.1	_	
	Storage time	t _{stg}		_	1.0	_	μs
	Fall time	t _f		_	0.1	_	

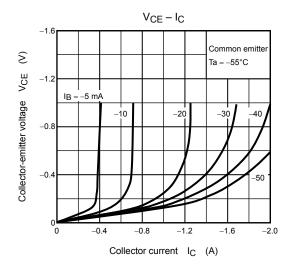
Note 3: $h_{FE\ (1)}$ classification O: 70 to 140, Y: 120 to 240

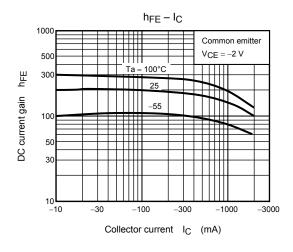
Marking

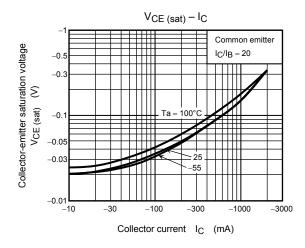


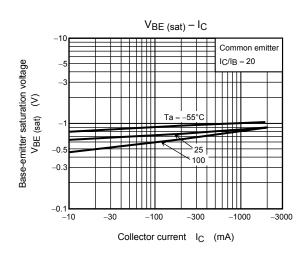


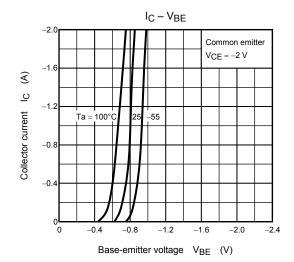


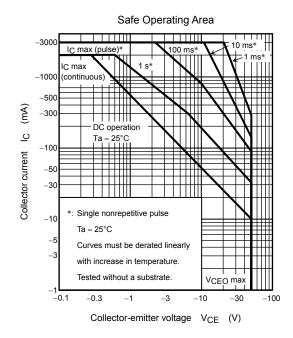


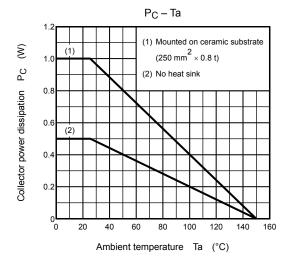












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20070701-EN

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